

IN THE CLAIMS

Please amend claims 1 and 17; cancel claims 31 and 43; and add new claims 65-69.

1. (Currently Amended) A method for electroplating a copper deposit onto a semiconductor integrated circuit device substrate with electrical interconnect features including submicron-sized features such that the surface has submicron-sized reliefs therein, the method comprising:

immersing the semiconductor integrated circuit device substrate into an electroplating bath including ionic copper and an effective amount of a defect reducing agent, wherein the defect reducing agent is a reaction product of benzyl chloride and hydroxyethyl polyethylenimine; and

electroplating the copper deposit from said bath onto the substrate to superfill ~~fill~~ the submicron-sized reliefs by rapid bottom up deposition within the reliefs whereby the occurrence of protrusion defects from superfilling, surface roughness, and voiding due to uneven growth are reduced, and macro-scale planarity across the semiconductor integrated circuit device substrate wafer is improved.

2. (Previously presented) The method of claim 1 wherein the defect reducing agent reduces high current density edge effect during the electroplating.

3. (Original) The method of claim 1 wherein the defect reducing agent improves distribution of deposited copper over the substrate surface.

4. (Original) The method of claim 1 wherein the deposit has a deposit thickness of about 1 micron and which varies by no more than about 0.2 microns across the deposit, the deposit thickness being measured from an upper surface of the deposit to the substrate surface at its thickest point.

5. (Original) The method of claim 1 wherein the defect reducing agent facilitates deposition of a thinner overall deposit to achieve a minimum thickness across the substrate than an overall deposit required to achieve such minimum thickness by electroplating without said defect reducing agent.

6. (Previously presented) The method of claim 1 further comprising removing a portion of the copper deposit by chemical and mechanical action to yield a level substrate, wherein an amount of copper deposit to be removed is less than an amount of copper deposit which must be removed by chemical and mechanical action to yield a level substrate in a comparable substrate electroplated without said defect reducing agent.

7. (Original) The method of claim 6 wherein pitting corrosion from said chemical action is less severe than pitting corrosion in the comparable substrate electroplated without said defect reducing agent.

8-16. (Canceled)

17. (Currently Amended) A method for electroplating a copper deposit onto a semiconductor integrated circuit

device substrate having electrical interconnect features including submicron-sized features such that the surface has submicron-sized reliefs therein, the method comprising:

immersing the semiconductor integrated circuit device substrate into an electroplating bath including ionic copper and an effective amount of a defect reducing agent which reduces a rate of recrystallization and grain growth in the copper deposit, thereby reducing the formation of internal voids within the copper deposit; and

electroplating the copper deposit from said bath onto the semiconductor integrated circuit device substrate to superfill ~~fill~~ the submicron-sized reliefs by rapid bottom up deposition within the reliefs, which deposit subsequently undergoes recrystallization and grain growth at a reduced rate and thereby is characterized by a reduced concentration of internal voids;

wherein the defect reducing agent is a reaction product of benzyl chloride and hydroxyethyl polyethylenimine.

18-30. (Canceled)

31. (Canceled)

32-42. (Canceled)

43. (Canceled)

44-64. (Canceled)

65. (New) The method of claim 1 wherein the electroplating bath further comprises sulfuric acid present in an amount between about 150 g/L and about 225 g/L.

66. (New) The method of claim 1 wherein a source of the ionic copper is copper sulfate pentahydrate present in an amount between about 59 g/L and about 75 g/L.

67. (New) The method of claim 1 wherein the electroplating bath comprises 1.0 mL/L of said defect reducing agent.

68. (New) The method of claim 1 wherein the electroplating bath comprises 2.0 mL/L of said defect reducing agent.

69. (New) The method of claim 1 wherein the electroplating bath comprises 5.0 mL/L of said defect reducing agent.